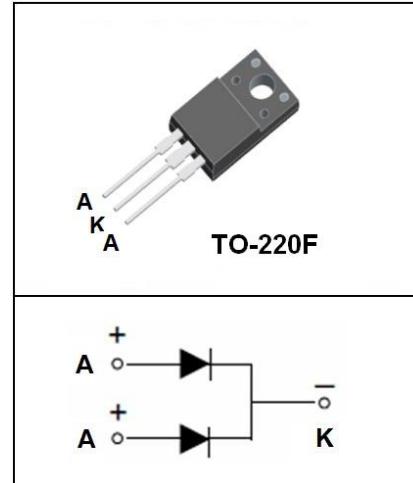


**MUR1060FCT****Ultra Fast Recovery Diode****●Features:**

- Common Cathode Structure
- Low Power Loss and High Efficiency
- Low Forward Voltage Drop
- High Surge Capability

●Application:

- High Frequency Switch
- Free Wheeling, and Polarity Protection Applications

**Absolute Maximum Ratings(Tc=25°C unless otherwise noted)**

Symbol	Parameter	Value	Unit
V _{RRM}	Maximum Repetitive Reverse Voltage	600	V
V _R	Maximum DC Reverse Voltage	600	V
I _{F(AV)}	Average Rectified Forward Current, Tc=120°C	5(Per Leg) 10(Per Device)	A
I _{FSM}	Peak Forward Surge Current, 8.3ms Half Sine wave	100	A
T _j	Operating Junction Temperature	150	°C
T _{stg}	Storage Temperature Range	-55 to +150	°C

Thermal Characteristics(Tc=25°C unless otherwise noted)

Symbol	Parameter	Max	Unit
R _{θJC}	Thermal Resistance, Junction to Case Per Leg	4.0	°C /W

Electrical Characteristics(Tc=25°C unless otherwise noted)

Symbol	Parameter	Test Conditions	Min	Max	Unit
V _{RRM}	Maximum Repetitive Reverse Voltage	I _R =100μA	600		V
I _R	Reverse Current	V _R =600V Tc=25°C V _R =600V Tc=125°C		0.1 5	mA
V _F	Forward Voltage	I _F =5A Tc=25°C I _F =5A Tc=125°C I _F =10A Tc=25°C I _F =10A Tc=125°C		1.40 1.30 1.50 1.40	V
T _{rr}	Maximum Reverse Recovery Time	I _F =0.5A I _R =1.0A I _{rr} =0.25A		50	ns



MUR1060FCT

Ultra Fast Recovery Diode

Typical Performance Characteristics

Figure 1. Forward Current Characteristics

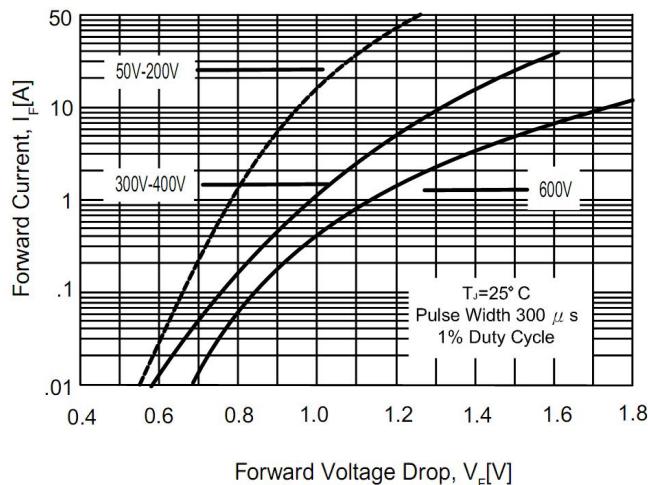


Figure 2. Reverse Leakage Current

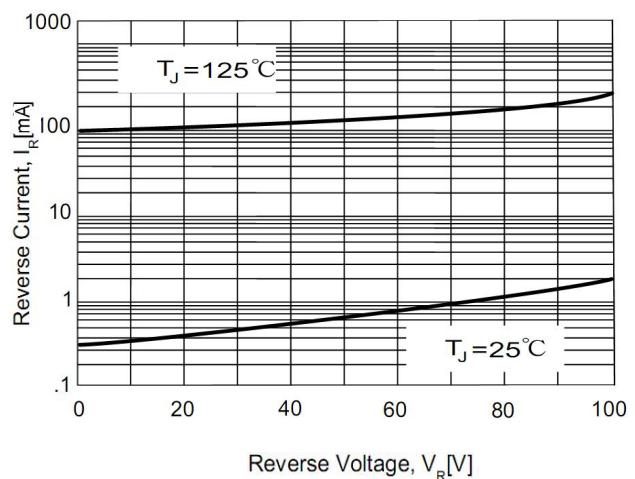


Figure 3. Junction Capacitance

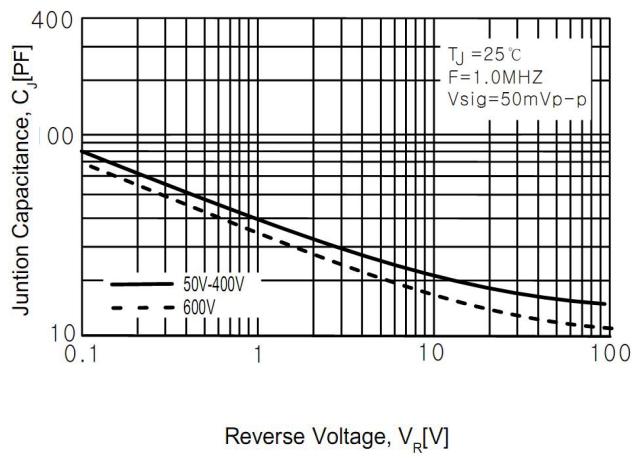
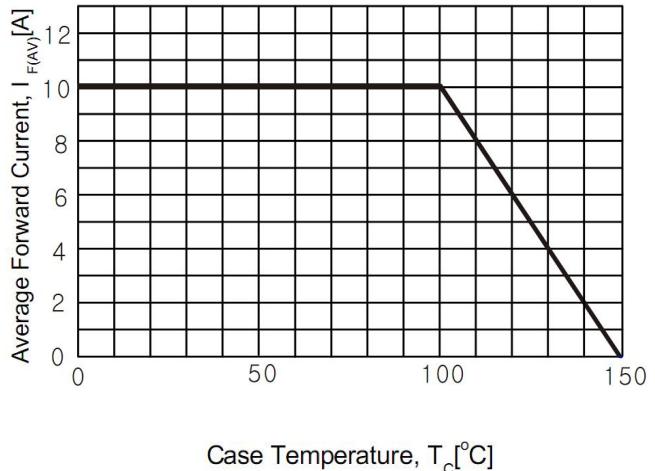


Figure 4. Power Derating





MUR1060FCT

Ultra Fast Recovery Diode

TO-220F Package Dimensions

UNIT: mm

SYMBOL	min	nom	max	SYMBOL	min	nom	max
A	9.80		10.60	D		2.54	
A1		7.00		D1	1.15		1.55
A2	2.90		3.40	D2	0.60		1.00
A3	9.10		9.90	D3	0.20		0.50
B1	15.40		16.40	E	2.24		2.84
B2	4.35		4.95	E1		0.70	
B3	6.00		7.40	E2		1.0×45°	
C	3.00		3.70	E3	0.35		0.65
C1	15.00		17.00	E4	2.30		3.30
C2	8.80		10.80	α (度)		30°	

